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(71)Applicant: SEMICONDUCTOR ENERGY LAB

CO LTD

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(72)Inventor: SATO MASAHIKO

KONUMA TOSHIMITSU

MASE AKIRA **TAKAYAMA TORU** OTAKA MASAICHI YAMAGUCHI TOSHIJI WATANABE TOSHIO AOYANAGI OSAMU TABATA KAORU ISHIGAKI CHIZURU

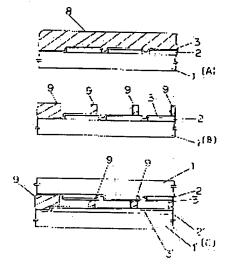
SAKAYORI HIROYUKI KOBAYASHI IPPEI

**OSABE AKIO** 

YAMAZAKI SHUNPEI

## (54) METHOD FOR FORMING LIQUID CRYSTAL ELECTROOPTICAL DEVICE (57) Abstract:

PURPOSE: To control a space between two orientation films to a prescribed thickness with scattering of  $\pm 0.5 \mu$ m by controlling a height of the orientated film to the prescribed height by remaining selectively an epoxy adhesives, and by forming a spacer and the peripheral sealing agent with the epoxy adhesives which is the same material to that of the spacer and sealing agent. CONSTITUTION: The titled device is formed by coating with the org. adhesives 8 such as the epoxy adhesives having photosensitive property on the one surface of the substrate 1 which forms an electrode 2, or forms an orientated film 3, thereon, in the prescribed height by means of a coating method followed by selectively exposing it with a mask to expose the photosensitive resin. The spacer 9 and the peripheral sealing part having a linear type, a block type or an optional adductor type are selectively formed by an etching step, after selectively exposing only a range which is not masked. Thus, even in case that the resin of acting as the spacer



and the peripheral sealing agent of a cell has the uneveness in height, the coating film of the prescribed thickness with scattering of less than  $\pm 0.5 \mu m$  is obtd. by selectively remaining the coating film which is the same material to that of the spacer and sealing agent.

## **LEGAL STATUS**

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